



**PATENT APPLICATION**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re application of

Docket No: Q80553

Toshiro HAYAKAWA

Appln. No.: 10/804,216

Group Art Unit: 2828

Confirmation No.: 6095

Examiner: Dung T. NGUYEN

Filed: March 19, 2004

For: SURFACE-EMITTING SEMICONDUCTOR LASER ELEMENT HAVING  
SELECTIVE-OXIDATION TYPE OR ION-INJECTION TYPE CURRENT-  
CONFINEMENT STRUCTURE, InGaAsP QUANTUM WELL, AND InGaP OR  
InGaAsP BARRIER LAYERS

**RESPONSE UNDER 37 C.F.R. § 1.111**

**MAIL STOP AMENDMENT**

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

Sir:

Responsive to the outstanding Office Action of August 1, 2006, once extended from  
November 1, 2006 to December 1, 2006 by the filing of an appropriate Petition and payment for  
extension of time submitted herewith, please consider Applicant's remarks as follows.

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